

Features

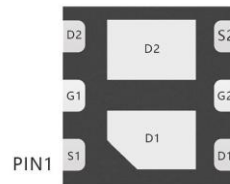
- Dual N-Channel
- TrenchFET Power MOSFET
- Low Gate Charge
- Low On-resistance
- Surface Mount Package

Application

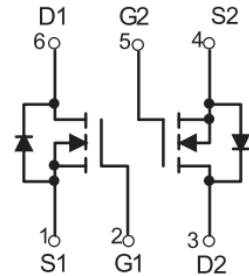
- Battery protection
- Load switch
- Power management

Product Summary

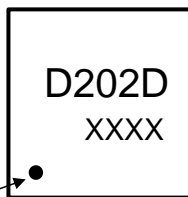
V_{DS}	$R_{DS(ON)}$ TYP	I_D
20V	360mΩ@4.5V	0.7A
	540mΩ@2.5V	



DFN2X2-6L view



Schematic diagram



D20D : Device code
 XXXX : Code

Pin 1

Marking and pin assignment



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	20	V
V_{GS}	Gate-Source Voltage	±12	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 0.7	A

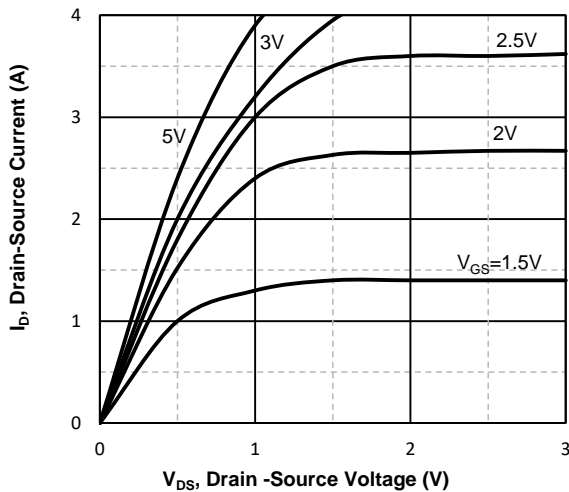
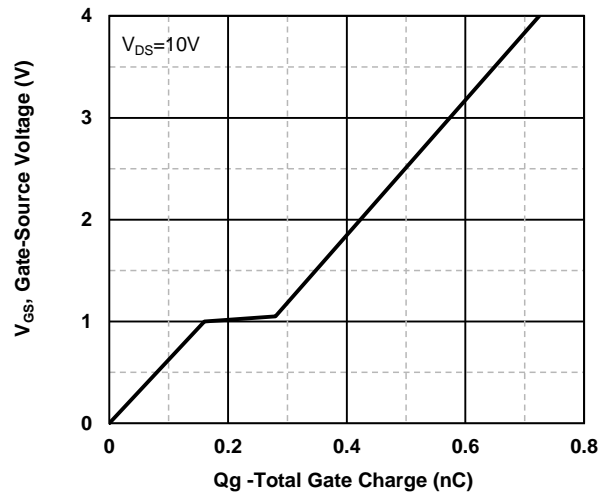
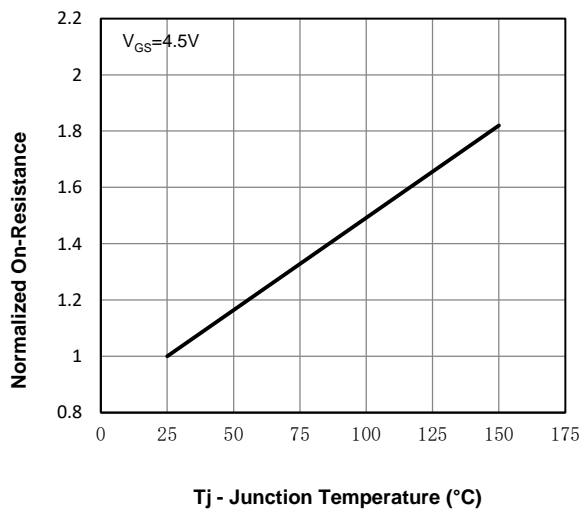
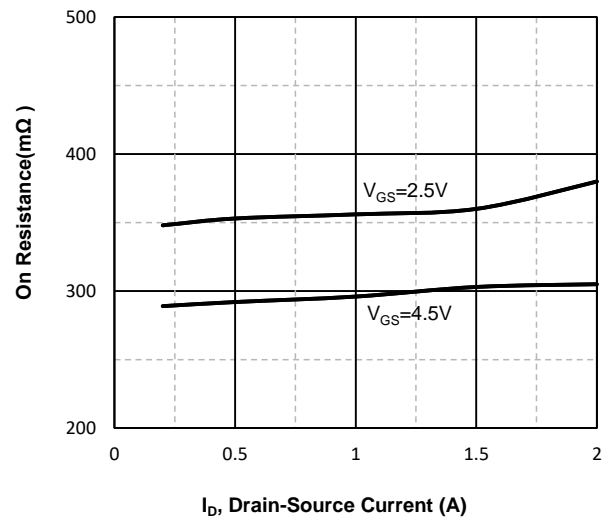
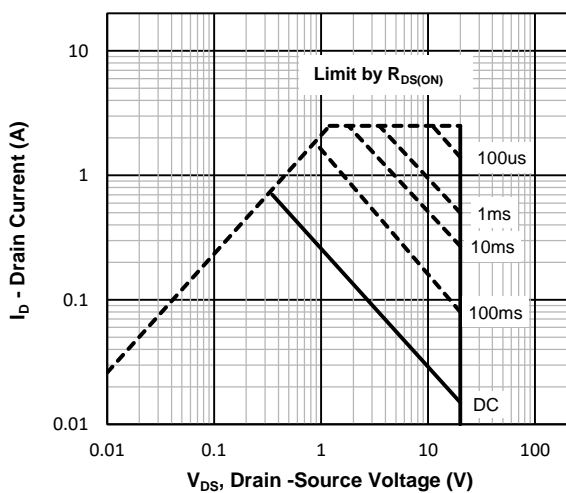
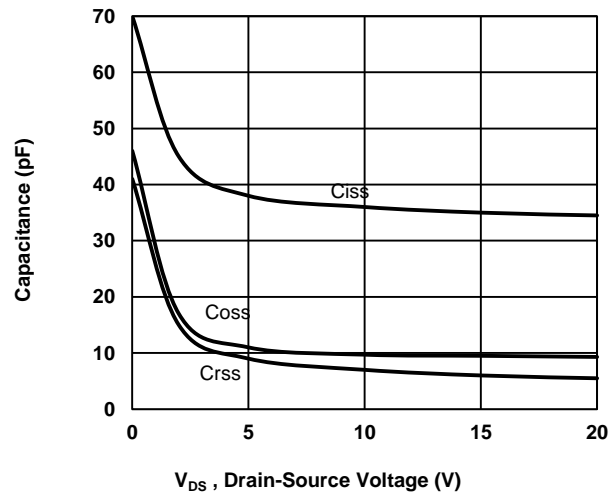
Mounted on Large Heat Sink

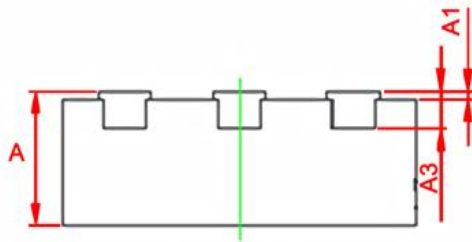
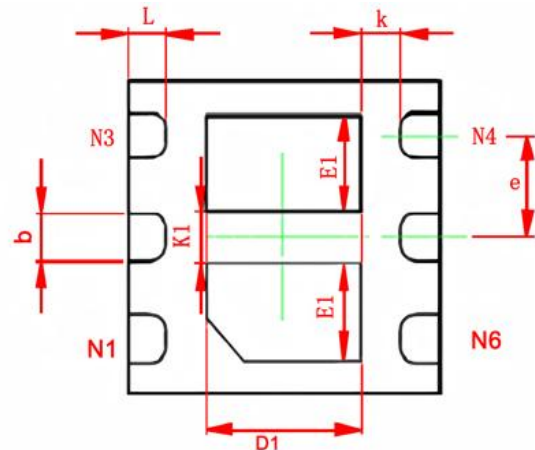
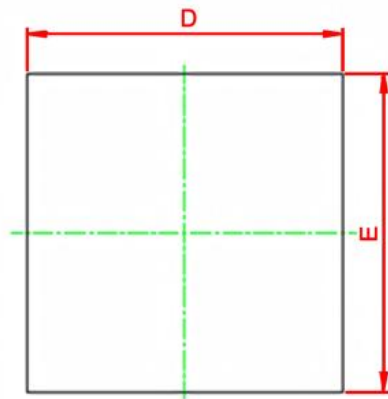
I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ 2.5	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ 0.7	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 0.75	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	100	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSMND202D	DFN2X2-6L	D202D	3,000	45,000	180,000	7" reel

Electrical Characteristics (T _J =25 °C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25 °C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	1.0	1.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _D =0.5A	--	360	450	mΩ
		V _{GS} =2.5V, I _D =0.4A	--	540	650	mΩ
Dynamic Electrical Characteristics @ T _J = 25 °C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	--	35	--	pF
C _{OSS}	Output Capacitance		--	9.5	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	8.8	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =10V, I _D =0.5A, V _{GS} =4.5V	--	0.8	--	nC
Q _{gs}	Gate Source Charge		--	0.1	--	nC
Q _{gd}	Gate Drain Charge		--	0.2	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =10V, I _D =0.5A, V _{GS} =4.5V, R _G =3Ω	--	7	--	nS
t _r	Turn-on Rise Time		--	10	--	nS
t _{d(off)}	Turn-Off Delay Time		--	35	--	nS
t _f	Turn-Off Fall Time		--	15	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25 °C, I _S =0.7A	--	0.8	1.2	V

Typical Operating Characteristics

Fig1. Typical Output Characteristics

Fig2. Typical Gate Charge Vs. Gate-Source Voltage

Fig3. Normalized On-Resistance Vs. Temperature

Fig4. On-Resistance Vs. Drain-Source Current

Fig5. Maximum Safe Operating Area

Fig6. Typical Capacitance Vs. Drain-Source Voltage

DFN2X2-6L Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.600	0.700	0.024	0.027
A1	0.000	0.050	0.000	0.001
A3	0.203REF		0.007REF	
b	0.230	0.330	0.009	0.012
D	1.924	2.076	0.075	0.081
E	1.924	2.076	0.075	0.081
e	0.650TYP		0.025TYP	
L	0.224	0.376	0.008	0.014
k	0.200	-	0.007	-
E1	0.520	0.720	0.020	0.028
D1	0.800	1.000	0.031	0.039
K1	0.320TYP		0.012TYP	